

Claims:

1. A method for treating disk-like objects with a first liquid and at least one second liquid at least in a defined edge region of a disk-like object, with the first liquid differing from the second liquid, characterized by the following successive steps:
 - 1.1 the disk-like object is brought close to a mask, with the distance a1 to the mask being equal to or larger than 0 mm and the mask overlapping with the disk-like object in the region in which the disk-like object is to be treated;
 - 1.2 application of the first liquid, so that the same is held in the region between the mask and the disk-like object;
 - 1.3 increasing the distance between the mask and the disk-like object to a distance a2;
 - 1.4 removal of the residues of the first liquid remaining on the disk-like object;
 - 1.5 reduction of the distance between the mask and the disk-like object to a distance b1;
 - 1.6 application of the second liquid, so that the same is held in the region between the mask and the disk-like object;
 - 1.7 increasing the distance between the mask and the disk-like object to a distance b2;
 - 1.8 removal of the residues of the second liquid remaining on the disk-like object.
2. A method as claimed in claim 1, wherein the first liquid removes a first layer from the disk-like object and the second liquid treats the uncovered surface.
3. A method as claimed in claim 2, wherein the second liquid etches the uncovered surface.
4. A method as claimed in claim 3, wherein the second liquid etches the uncovered surface in such a way that the second layer situated underneath is removed.
5. A method as claimed in claim 1, wherein the distance a2 or b2 is at least one and a half times as large as the distance a1 or b1.
6. A method as claimed in claim 1, wherein at least one of the at least two liquids is applied to the side averted from the mask, flows around the circumferential edge of the disk-like object and then penetrates the region between the mask and the disk-like object.
7. A method as claimed in claim 2, wherein at least one layer is removed at least partly on the side averted from the mask.
8. A method as claimed in claim 2, wherein at least one of the materials of a layer consists of the group comprising silicon dioxide (thermal oxide, TEOS (tetraethoxysilane)), silicon nitride, titanium, titanium nitride, tantalum, tantalum nitride, cobalt, gold, silver, platinum, tungsten, tungsten silicide, polysilicon, copper, aluminum, silicate glass (fluorinated silicate glass, boron silicate glass (BSG), phosphorus boron silicate glass (PBSG), phosphorus silicate glass (PSG), undoped silicate glass (USG)), boron strontium titanate (BST), lead zirconium titanate (PZT).

9. A method as claimed in claim 8, wherein at least one of the materials of a layer is of the group consisting of titanium, titanium nitride, tantalum, tantalum nitride, cobalt, gold, silver, platinum, tungsten, tungsten silicide, polysilicon (polycrystalline silicon), copper, aluminum, and another material from the group of silicon nitride, silicon dioxide, silicate glass.
- 5 10. A method as claimed in claim 1, wherein the removal of the residues of the first etching solution remaining on the disk-like object occurs in such a way that the remaining residues of the first etching solution are ejected off.
11. A method as claimed in claim 1, wherein the removal of the residues of the first etching solution remaining on the disk-like object occurs by scouring with a liquid.
- 10 12. A method as claimed in claim 1, wherein the increase or decrease of the distance between the mask and the disk-like object occurs by lifting or lowering the disk-like object.
13. A method as claimed in claim 1, wherein the lifting or the lowering of the disk-like object occurs in such a way that the surface of the disk-like object facing the mask is flowed against via gas nozzles, namely by a respective change made to the speed component of
- 15 the gas stream which acts normally on the surface of the disk-like object.
14. A method as claimed in claim 1, wherein the disk-like object is held on the circumferential side by grasping elements during etching treatment.
15. A method as claimed in claim 14, wherein the grasping elements are not in contact during the lifting and lowering of the disk-like object.